

Spin Hall effect

Egy kis spintronika

Spin-pálya kölcsönhatás

Miért nem szeretjük a spin-pálya kölcsönhatást?

Miért szeretjük mégis?

A spin-injektálás buktatói

Spin Hall effect: a kezdetek

Dyakonov - Perel 1971

Hirsch 1999

SOI és aszimmetrikus szórás: skew scattering, side jump

Extrinsic vs. intrinsic origin

Méréstechnikai buktatók

Spin Hall effect: kísérleti igazolás

Optika: Awschalom 2004, Wunderlich 2005

Nem-lokális transzport: Valenzuela & Tinkham 2006

Spin Hall effect: elméleti kitekintés

SHE, AHE, OHE...

Spin mágneses térben (Zeeman effektus)

Spin operátor $\mathbf{S} = \frac{1}{2}\boldsymbol{\sigma}$

Pauli mátrixok $\sigma_x = \begin{pmatrix} 0 & 1 \\ 1 & 0 \end{pmatrix}$ $\sigma_y = \begin{pmatrix} 0 & -i \\ i & 0 \end{pmatrix}$ $\sigma_z = \begin{pmatrix} 1 & 0 \\ 0 & -1 \end{pmatrix}$

Mágneses momentum $\boldsymbol{\mu} = -\frac{1}{2}g\mu_B\boldsymbol{\sigma}$ $\mu_B = |e|\hbar/2m_e$

$$g = 2.0023$$

A spinre ható forgatónyomaték
homogén mágneses térben

$$\mathbf{M} = \boldsymbol{\mu} \times \mathbf{B}$$

Hamilton operátor

$$H = -\boldsymbol{\mu}\mathbf{B} = \frac{1}{2}g\mu_B\boldsymbol{\sigma}\mathbf{B}$$

Energia sajátértékek

$$E_{\pm} = \pm \frac{1}{2}g\mu_B B$$

Zeeman felhasadás

Spin elektromos térben (Spin-pálya kölcsönhatás)

Külső elektromos térben mozgó elektron a vele mozgó vonatkoztatási rendszerben egy mágneses teret is érez (Lorentz trf.):

$$\mathbf{B}' = -\frac{1}{c^2} \mathbf{v} \times \mathbf{E}$$

A mágneses momentum v/c rendben nem változik.

Naivan:
$$H'_{SO} = g\mu_B \mathbf{B}' \cdot \mathbf{S}' = -g\mu_B \frac{1}{c^2} (\mathbf{v} \times \mathbf{E}) \cdot \mathbf{S} = H_{SO}$$

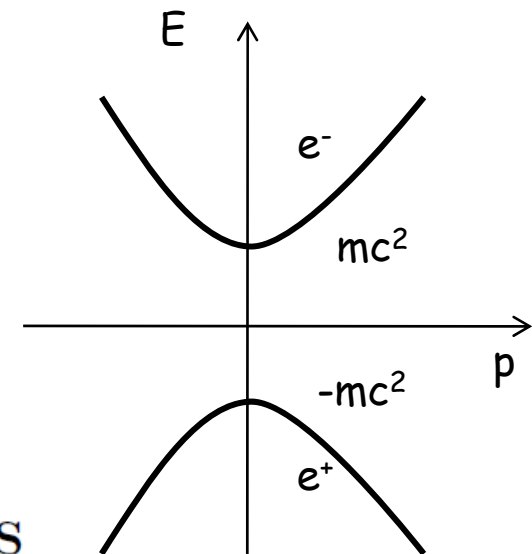
Precízebben: Dirac egyenlet nem-relativisztikus sorfejtésével

$$\begin{pmatrix} E - mc^2 & -c\boldsymbol{\sigma}\boldsymbol{\pi} \\ -c\boldsymbol{\sigma}\boldsymbol{\pi} & E + mc^2 \end{pmatrix} \boldsymbol{\Psi} = 0 \quad E = \pm \sqrt{c^2 p^2 + m^2 c^4}$$

$$H = mc^2 + V + \frac{p^2}{2m} - \frac{p^4}{8m^3 c^2} - \frac{\hbar c}{4mc^2} (\boldsymbol{\sigma} \cdot \nabla V) + \frac{\hbar^2}{8m^2 c^2} \Delta V$$

Spin-pálya

$$H_{SO} = -\frac{g\mu_B}{2} \frac{1}{c^2} (\mathbf{v} \times \mathbf{E}) \cdot \mathbf{S} = \frac{g\hbar}{4c^2 m_e^2} (\nabla V(\mathbf{r}) \times \mathbf{p}) \cdot \mathbf{S}$$



Erős félvezetős analógia!

SOI hatása a sáv szerkezetre

- » Nehezebb elemek - erősebb gradiens az atomi potenciálokban - erősebb SOI kristályokban is igaz (Si < Ge < GaAs)
- » SOI csökkenti a szimmetriát - további degenerációk oldódnak fel (SO split-off band)

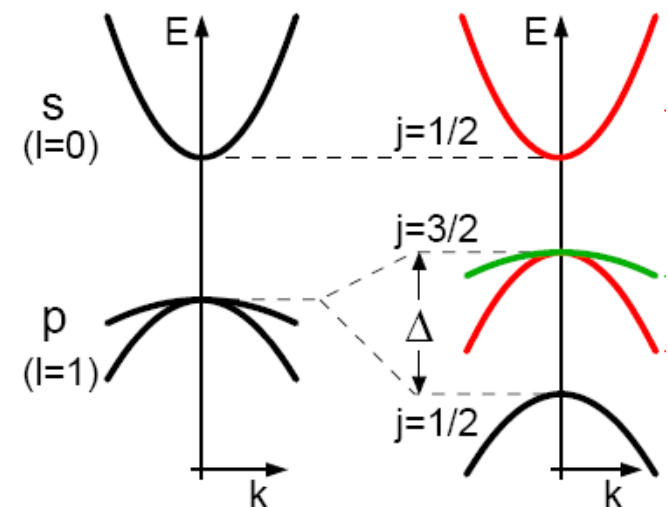
$$\left. \begin{array}{l} \text{Inverziós szimmetria} \\ \text{Időtükrozési szimmetria} \end{array} \right\} \begin{array}{l} \mathbf{k} \rightarrow -\mathbf{k} \\ S_z \rightarrow -S_z \end{array} \quad E_{\uparrow}(\mathbf{k}) = E_{\downarrow}(\mathbf{k})$$

inverzió szimmetria nélküli zinc blende félvezetők (GaAs, InAs, InSb):

Bulk Inversion Asymmetry Dresselhaus SOI $E_{+}(\mathbf{k}) = E_{-}(-\mathbf{k})$

2DEG aszimmetrikus kvantumgödörben:
Structure Inversion Asymmetry, Rashba SOI

„beépített” elektromos tér a háromszög potenciál miatt, hasonlóan mint a Datta-Das tranzisztornál



Spin-orbit interaction in 2DEGs

$$H = H_0 + \alpha_R(\sigma_x k_y - \sigma_y k_x) + \beta_D(\sigma_x k_x - \sigma_y k_y)$$

SIA

$$\alpha_R = \alpha \langle E_z \rangle,$$

Built in and external electric fields

k-dependent spin-orbit induced magnetic field:

$$\mathbf{B}_{\text{SO}}(\mathbf{k}) = \frac{2}{g\mu_B} \begin{pmatrix} \alpha_R k_y + \beta_D k_x \\ -\alpha_R k_x - \beta_D k_y \\ 0 \end{pmatrix}$$

$$g\mu_B \mathbf{B}_{\text{SO}}(\mathbf{k}) \boldsymbol{\sigma} / 2.$$

$$E_{\pm} = \frac{\hbar^2 k_{\parallel}^2}{2m^*} \pm \alpha_R k_{\parallel} \quad k_{\parallel} = \sqrt{k_x^2 + k_y^2}$$

Parabolae shifted in **k** by $\pm m^* \alpha_R / \hbar^2$.

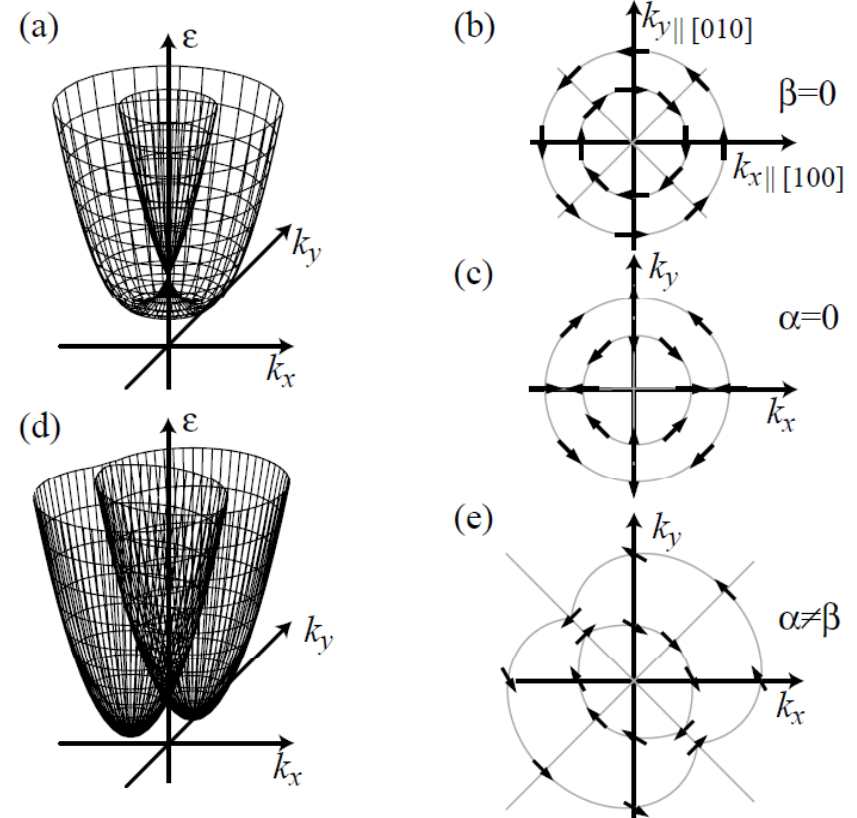
Same for the Dresselhaus term

$$\frac{\Delta E_{\text{SO}}}{E_F} = \frac{4\alpha_{R/D} m^*}{\hbar^2 k_F}$$

BIA

$$\beta_D = \beta \langle k_z^2 \rangle$$

Band structure and QW width



Spin-pálya kölcsönhatás (SOI) vs. Spintronika

Miért nem szeretjük?

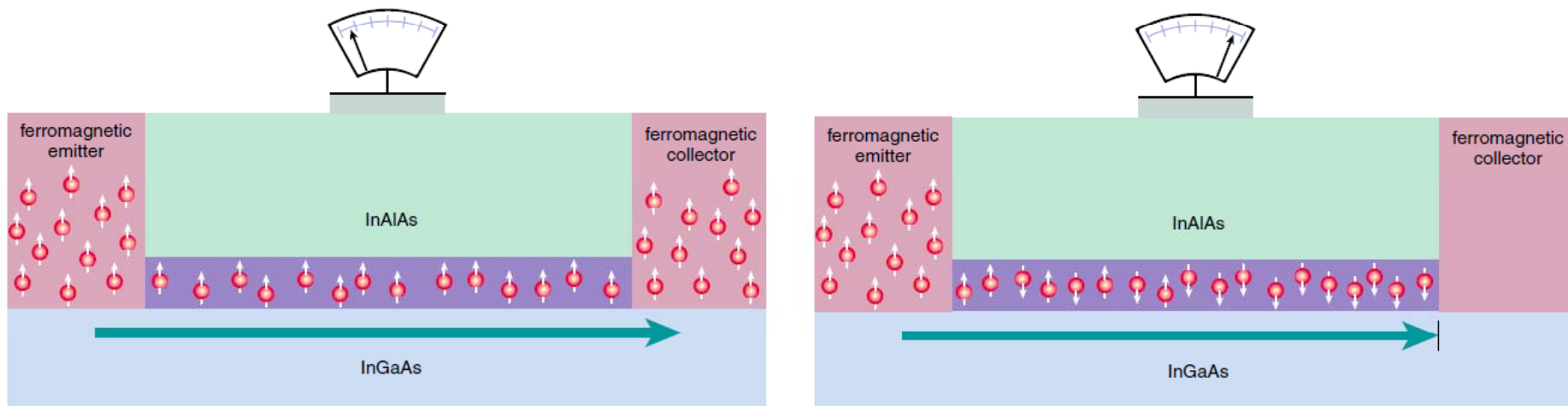
Preferált spin irányok minden egyes k irányhoz \rightarrow a momentum szórások spin szórással járnak együtt \rightarrow gyors spinrelaxáció (információ vesztes)

Miért szeretjük mégis?

Alacsonyabb dimenziókban a k -tér erősen redukált \rightarrow a momentum szórások kisebb hányada jár spin szórással \rightarrow hosszabb spinrelaxációs idők

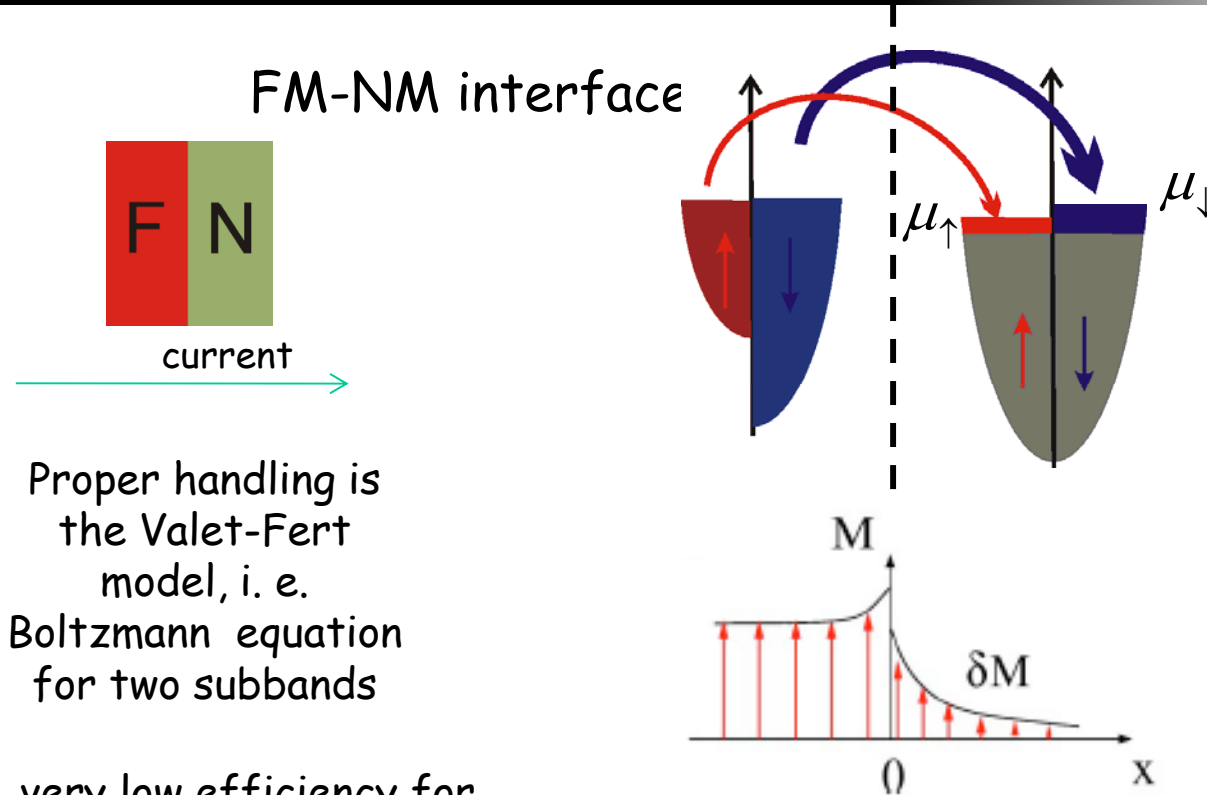
A spin csatolódik a töltéshez és a momentumhoz \rightarrow spin manipuláció mágneses tér nélkül, tisztán kapufeszültségekkel! - gyors, leskálázható

Datta-Das transistor



S. Datta and B. Das, APL **56**, 665 (1990).

Spin injection and detection



spin imbalance of the current results in a different chemical potential for the two subbands, which decays in bulk

This is detected in the GMR experiment

diffusive spin transport

associated lifetime τ_s and length scale l_s

$$\frac{\beta^2}{1 - \beta^2} \frac{\lambda_{\text{fm}}^2}{\sigma_{\text{fm}}^2} \frac{\sigma_{\text{sc}}^2}{x_0^2} \frac{4}{\left(2 \frac{\lambda_{\text{fm}} \sigma_{\text{sc}}}{x_0 \sigma_{\text{fm}}} + 1\right)^2 - \beta^2}$$

interface spin loss $\delta_{F/N}$

$$l_s = \sqrt{D \tau_s} \quad \text{with} \quad \tau_m \ll \tau_s$$

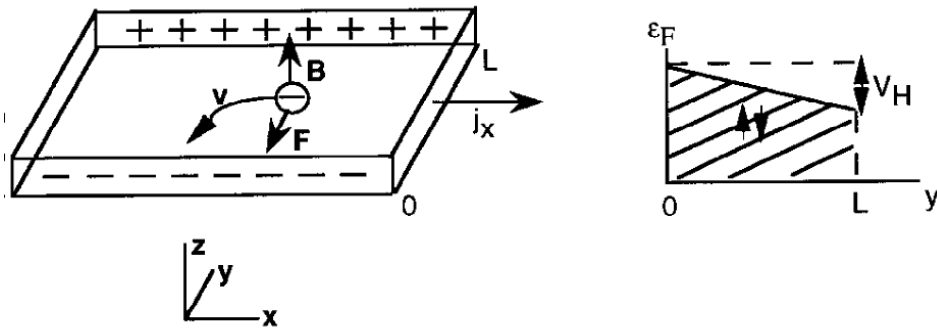
$$D = \frac{1}{3} v_F l_m$$

Spin Hall effect: J. E. Hirsch, 1999

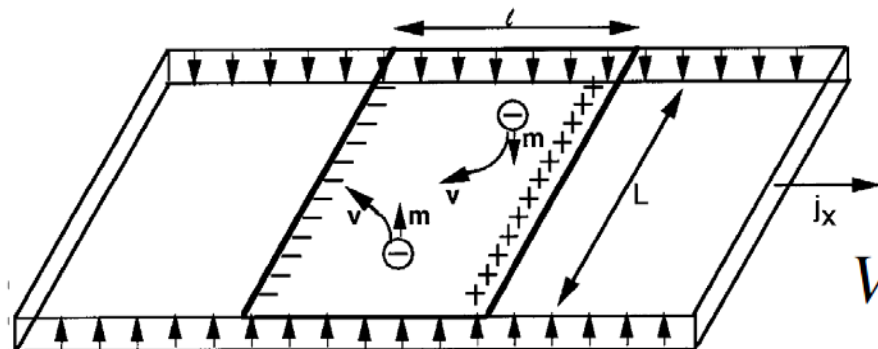
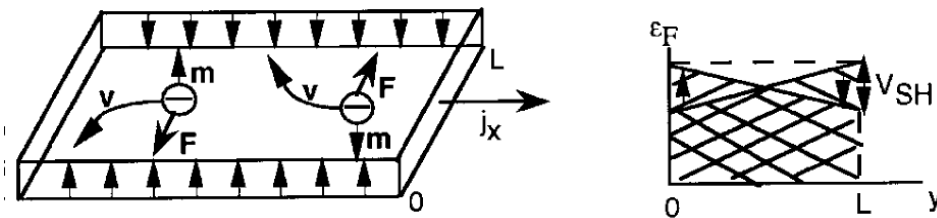
M. I. Dyakonov and V. I. Perel, Phys. Lett. **35A**, 459 (1971).

J. E. Hirsch, PRL **83**, 1834 (1999).

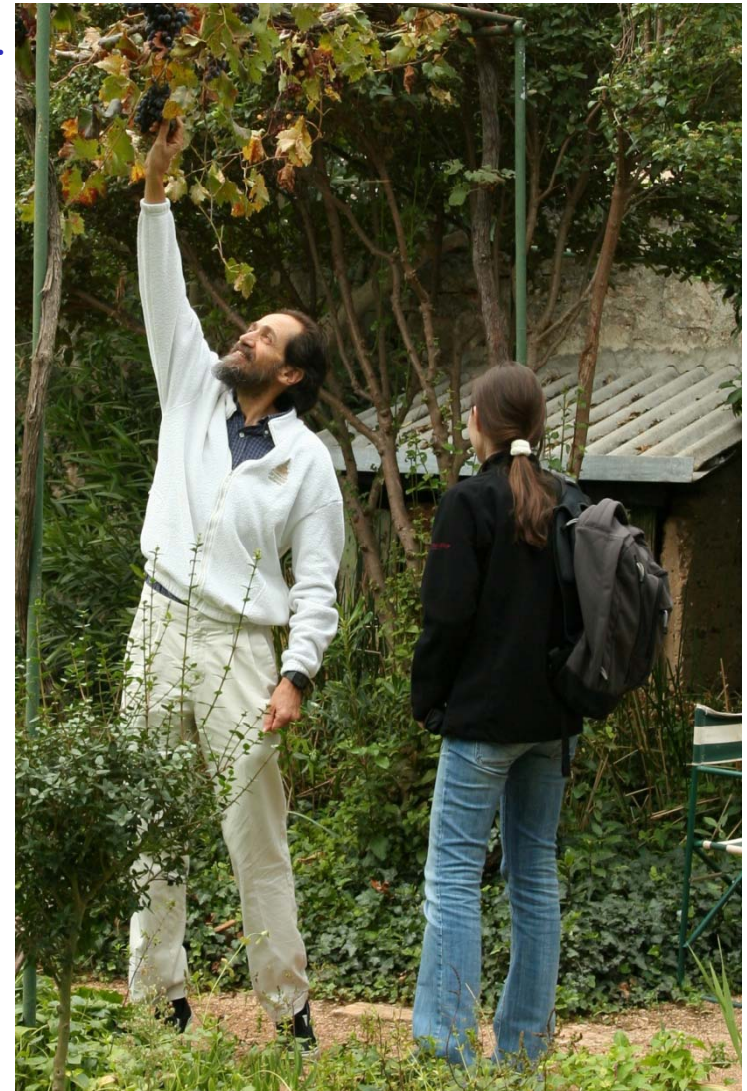
Hall effect



Spin Hall effect



$$V_{SH}^{\sigma} = 4\pi R_s l j_{\sigma} n_{\sigma} \mu_B \sim 50 \text{ nV}$$

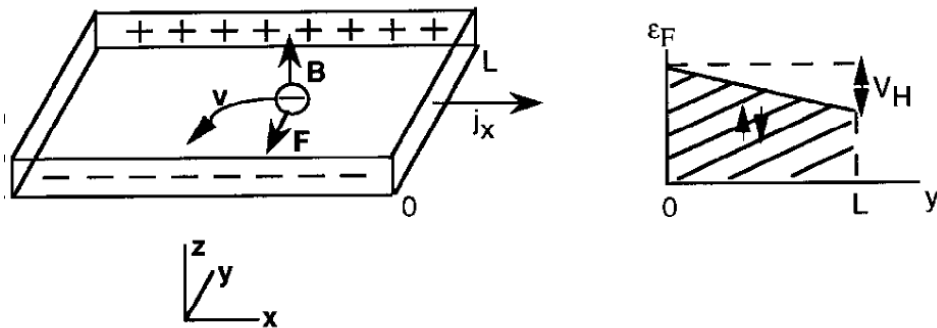


Spin Hall effect: J. E. Hirsch, 1999

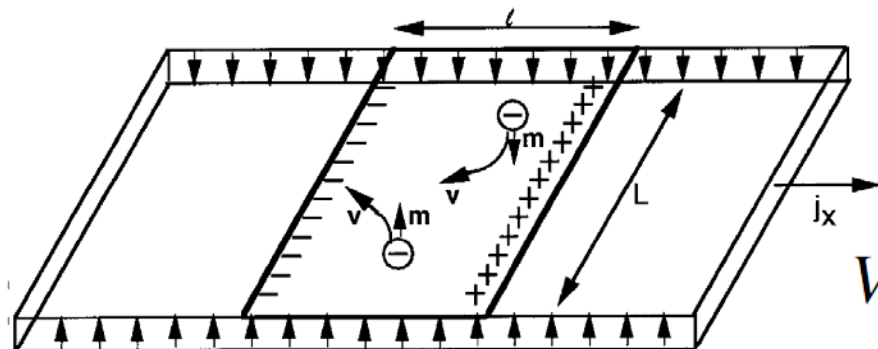
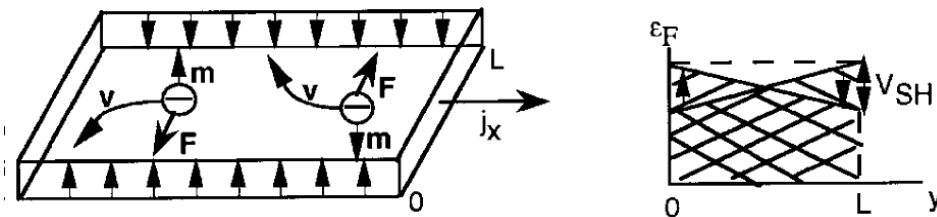
M. I. Dyakonov and V. I. Perel, Phys. Lett. **35A**, 459 (1971).

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Hall effect



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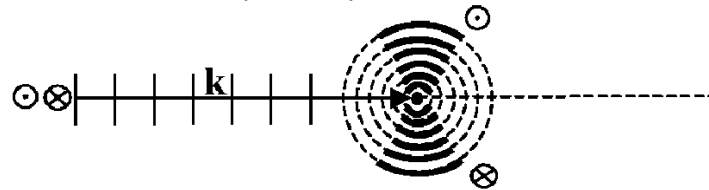
Kísérleti nehézségek

- Áram mágneses tere
- FM elektródák anizotróp mágneses ellenállása
- Hagyományos Hall effektus, AHE

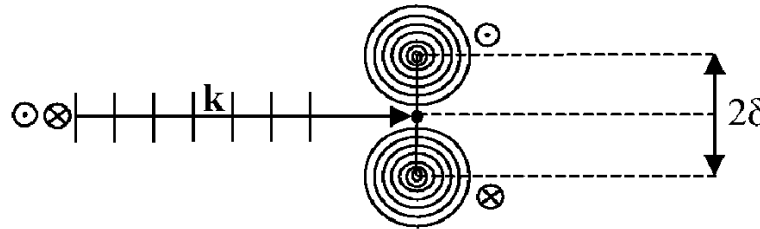
Spin Hall effect: SOI and asymmetric spin scattering

A. Crépieux and P. Bruno, PRB 64, 014416 (2001).

Skew scattering



Side-jump



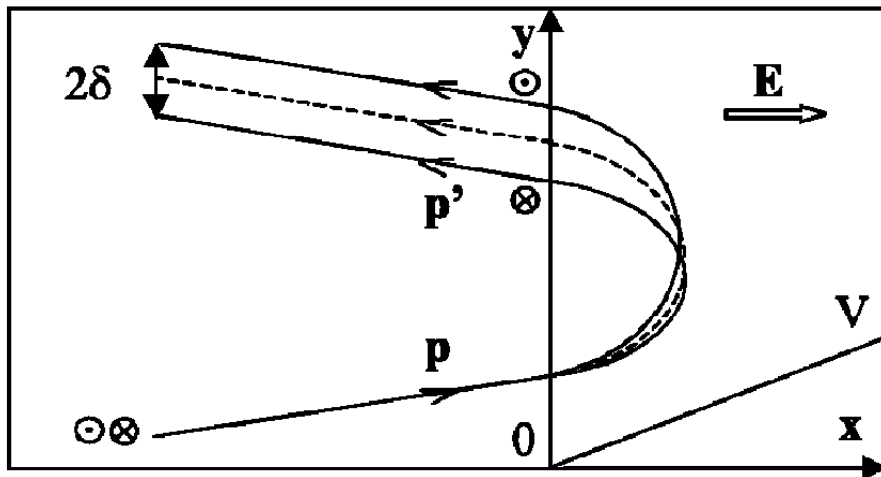
Kvázi-klasszikus magyarázat

$$H = \frac{p^2}{2m} - \mu_B (\boldsymbol{\sigma} \cdot \mathbf{B}_{\text{eff}}) + V + \frac{\hbar}{4m^2 c^2} (\boldsymbol{\sigma} \times \nabla V) \cdot \mathbf{p}$$

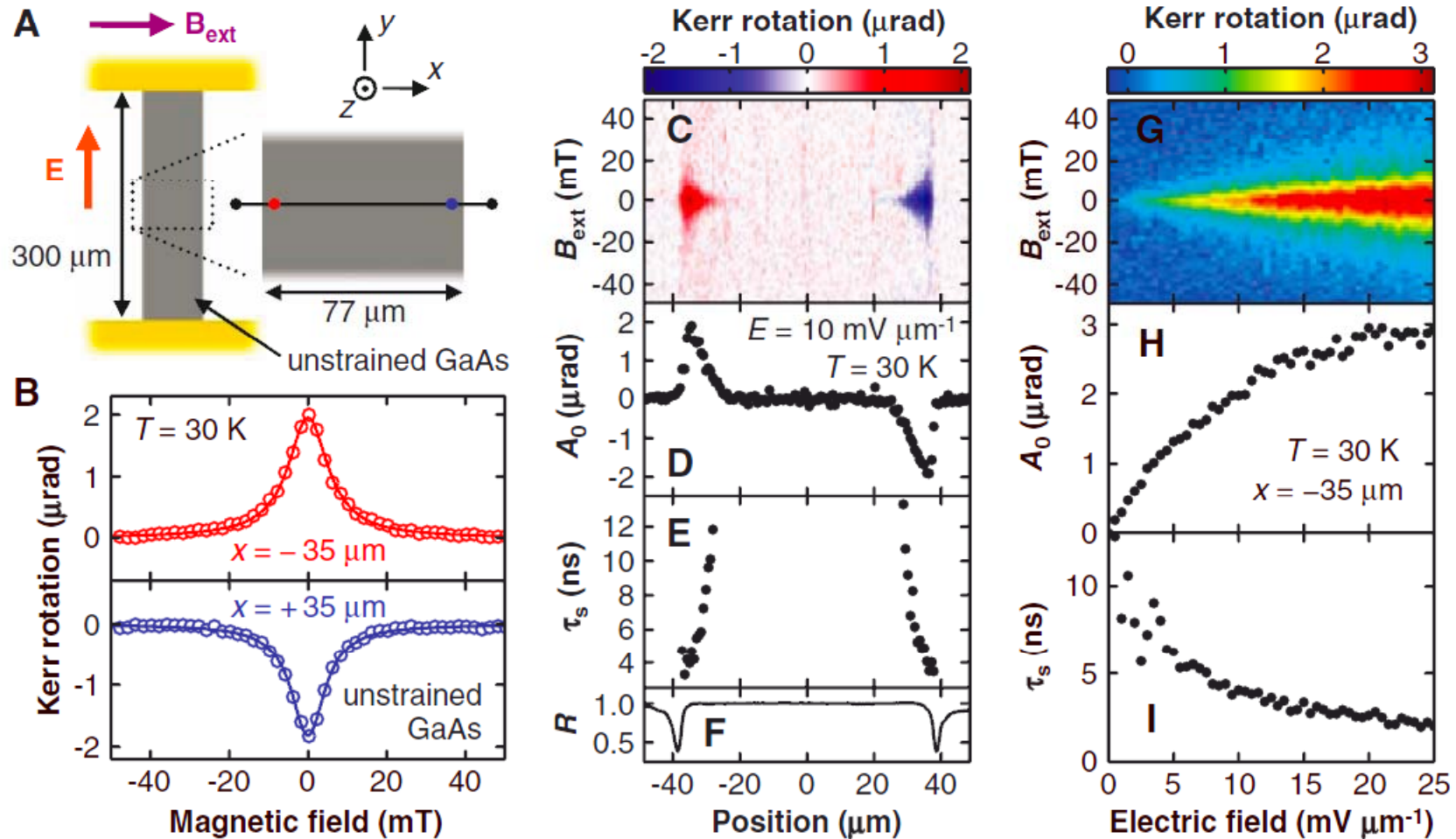
$$\mathbf{v} = \frac{\partial H}{\partial \mathbf{p}} = \frac{\mathbf{p}}{m} - \frac{e\hbar}{4m^2 c^2} (\boldsymbol{\sigma} \times \mathbf{E})$$

$$\delta = \int_{-\infty}^{+\infty} \mathbf{v}_a dt = - \int_{-\infty}^{+\infty} \frac{e\hbar}{4m^2 c^2} (\boldsymbol{\sigma} \times \mathbf{E}) dt$$

$$\delta = - \frac{\hbar \boldsymbol{\sigma}}{4m^2 c^2} \times \int_{-\infty}^{+\infty} d\mathbf{p} = \frac{\lambda^2 \boldsymbol{\sigma}}{4\hbar} \times (\mathbf{p} - \mathbf{p}')$$

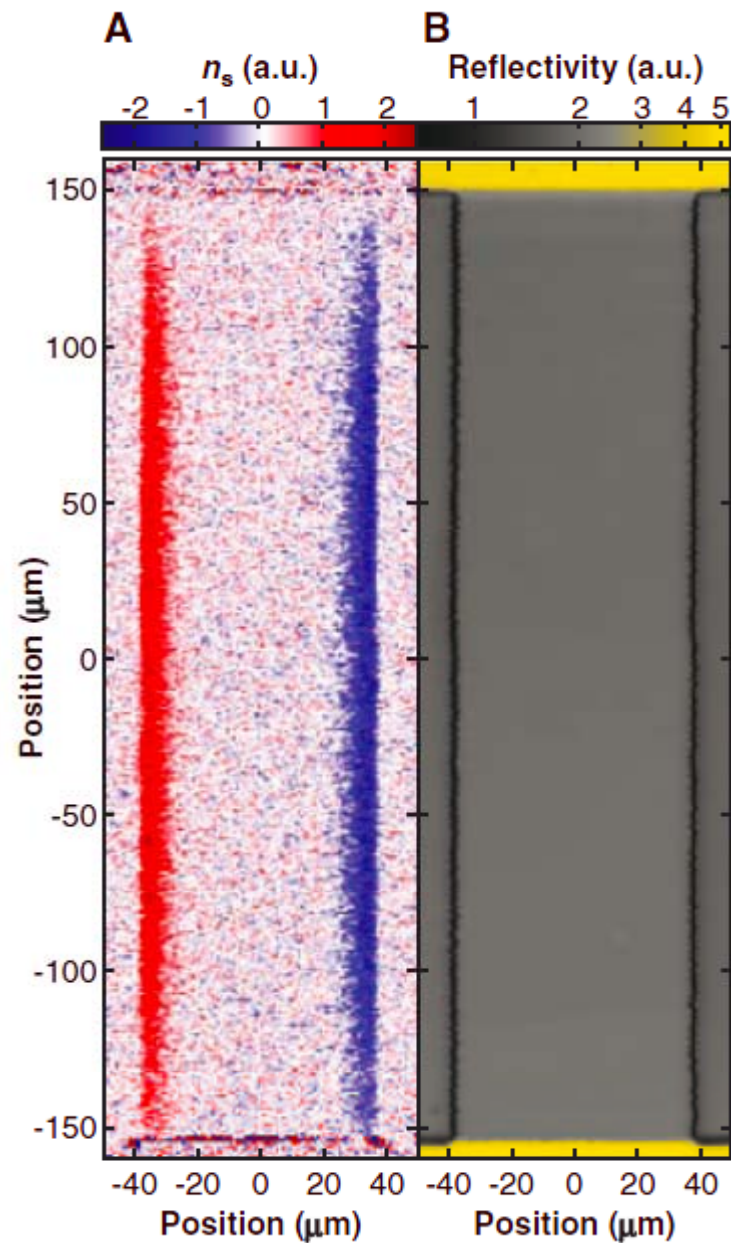


Spin Hall effect: experimental evidence 1



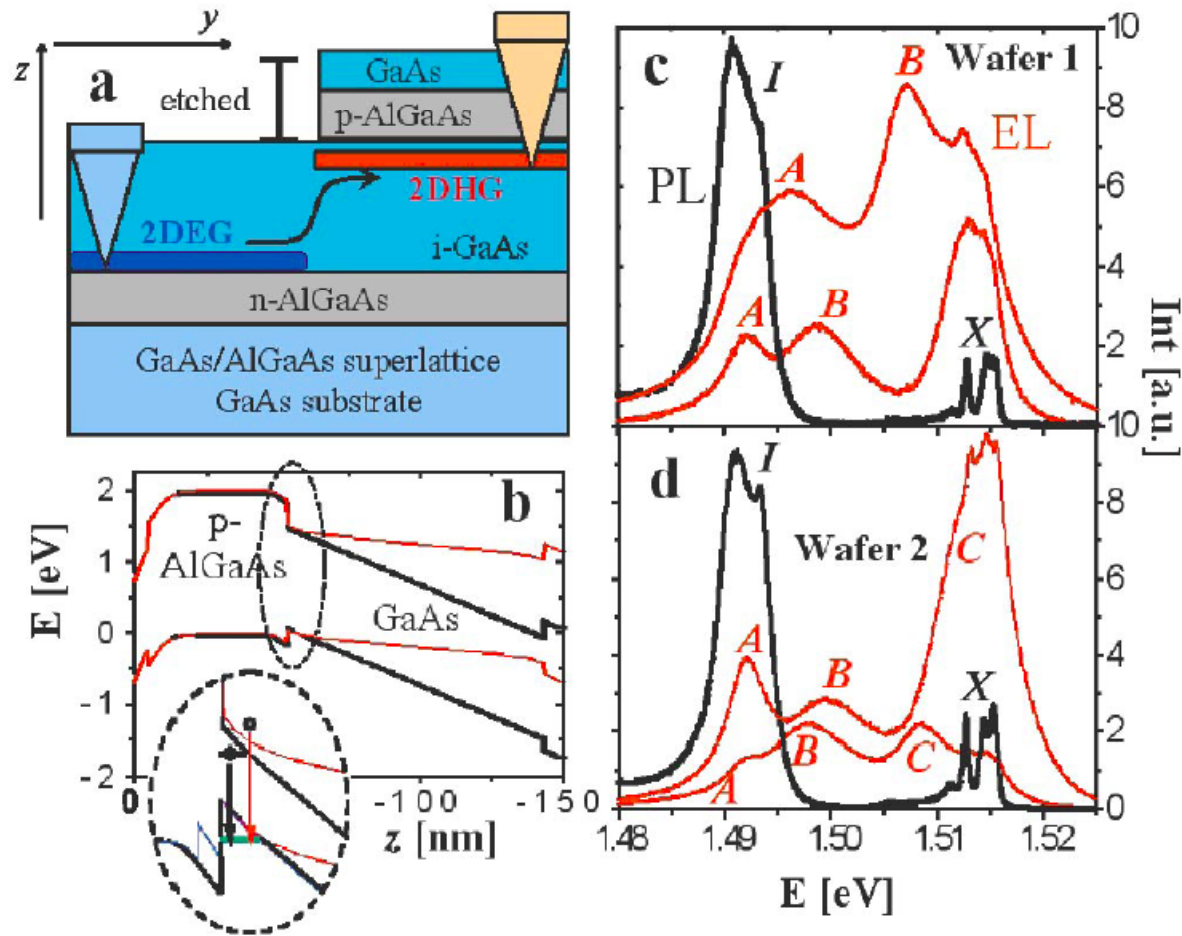
Y. K. Kato *et al.*, *Science* **306**, 1910 (2004).

Spin Hall effect: experimental evidence 1

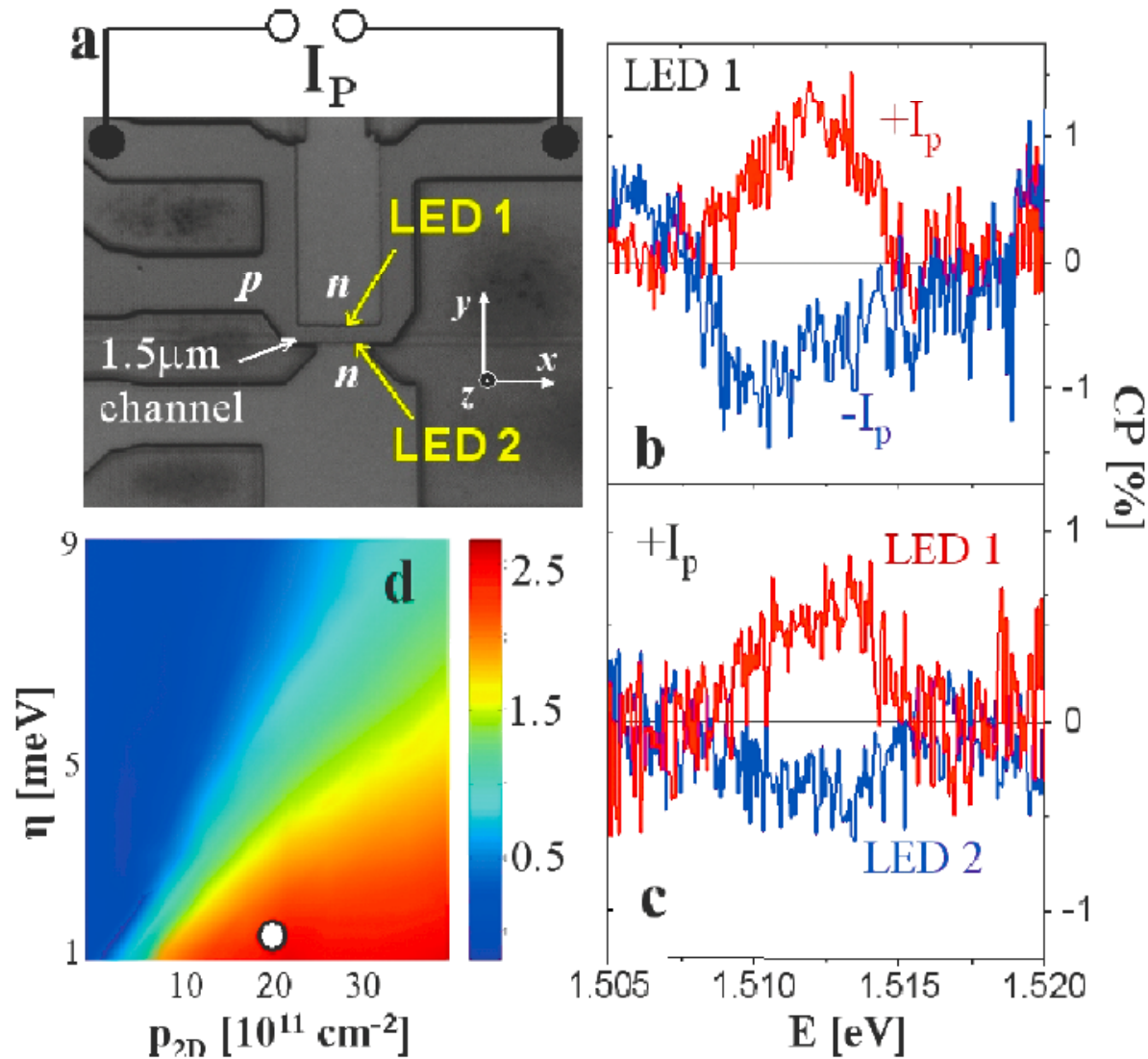


Y. K. Kato *et al.*, *Science* **306**, 1910 (2004).

Spin Hall effect: experimental evidence 2

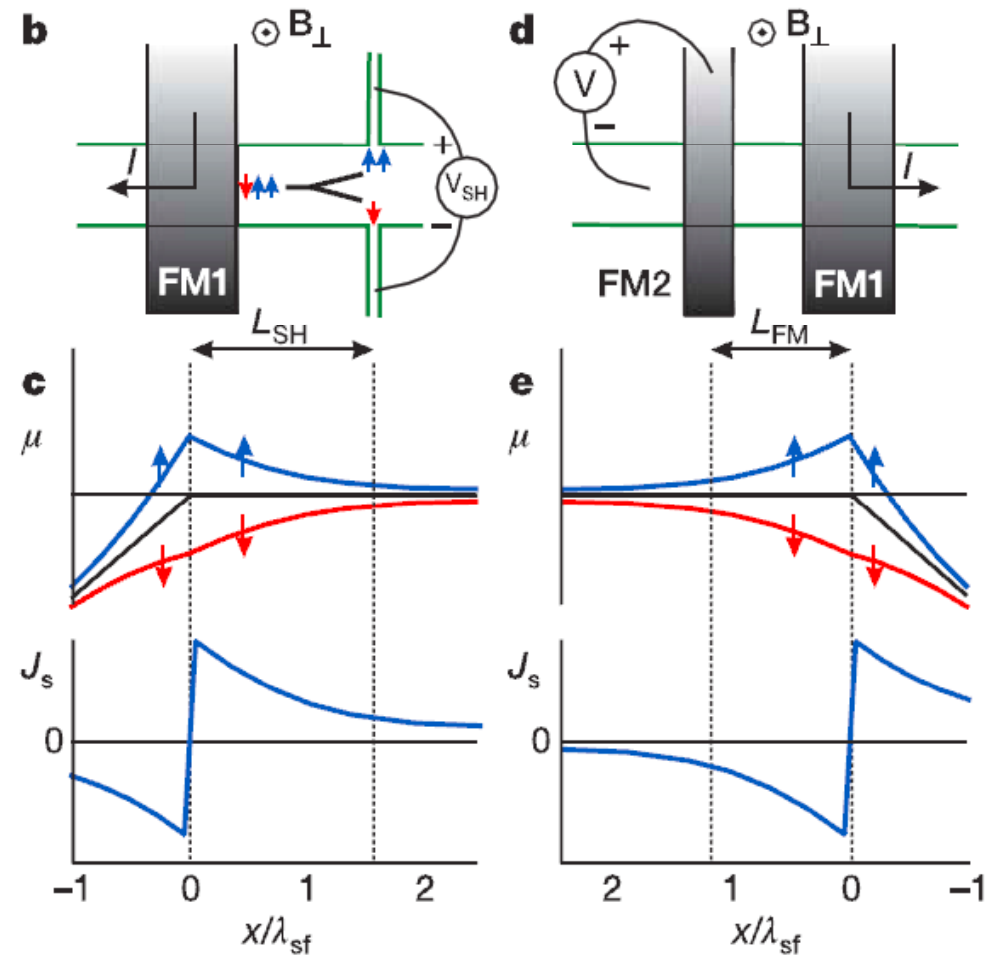
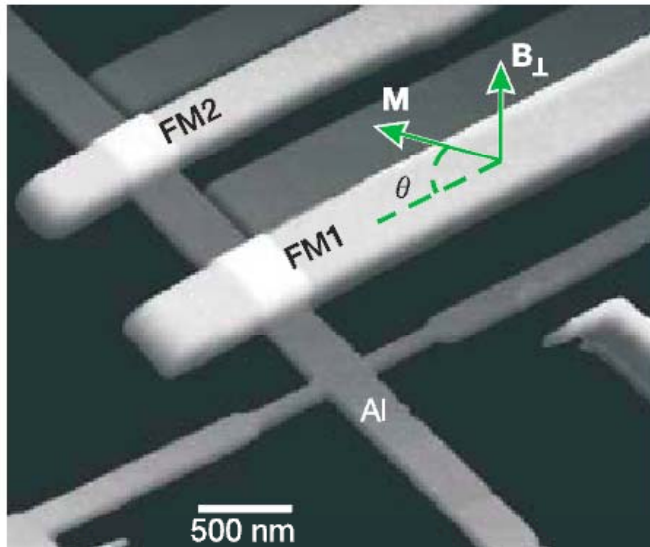


Spin Hall effect: experimental evidence 2



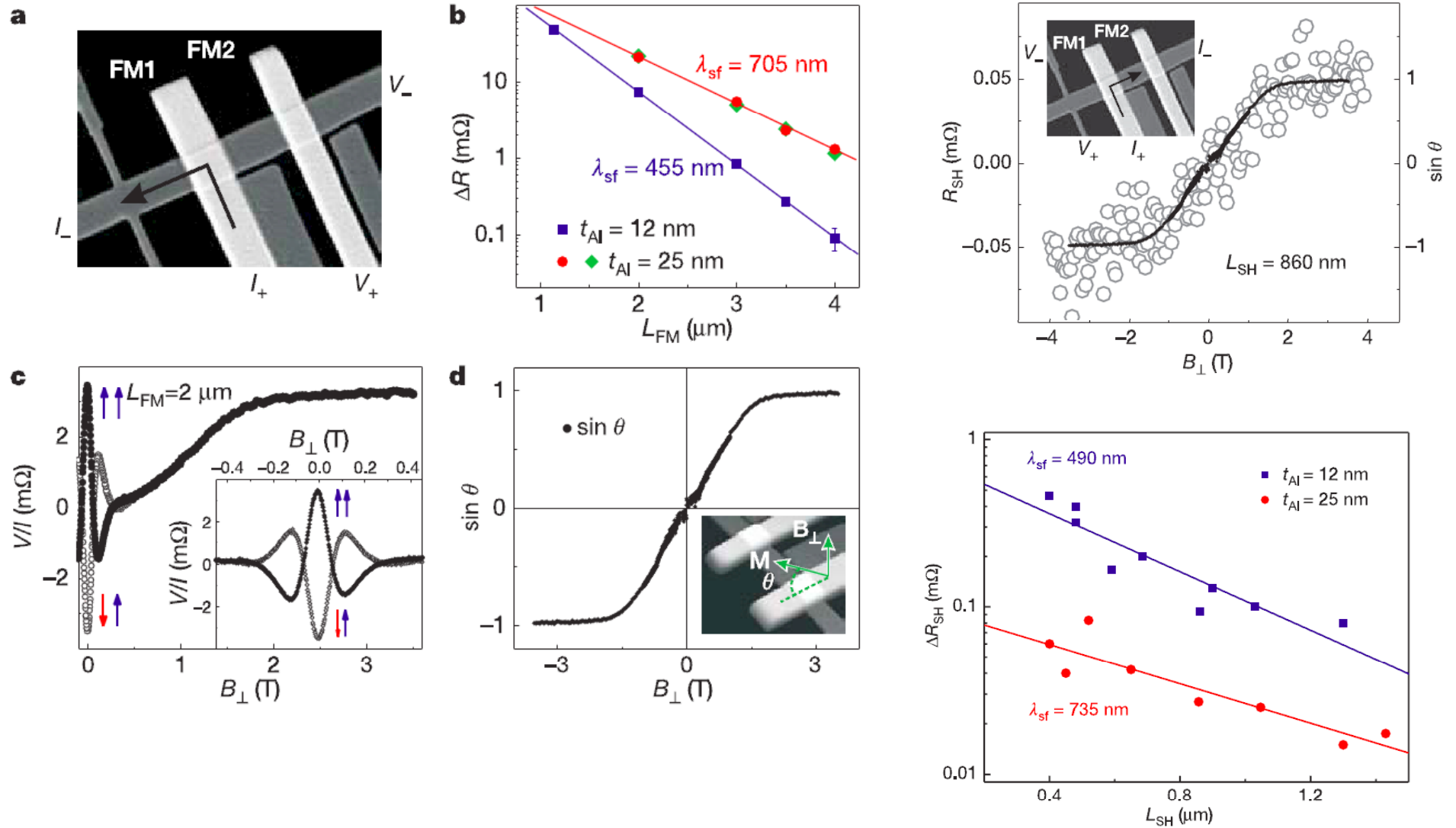
J. Wunderlich *et al.*, PRL **94**, 047204 (2005).

Spin Hall effect: experimental evidence 3



S. O. Valenzuela and M. Tinkham, Nature **442**, 176 (2006).

Spin Hall effect: experimental evidence 3



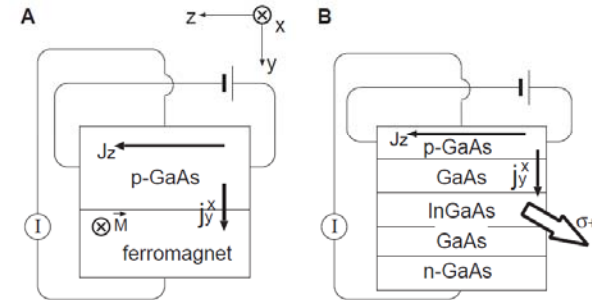
S. O. Valenzuela and M. Tinkham, *Nature* **442**, 176 (2006).

Spin Hall effect: theory outlook

Dissipationless Quantum Spin Current at Room Temperature

Shuichi Murakami,^{1*} Naoto Nagaosa,^{1,2,3} Shou-Cheng Zhang⁴

1348 5 SEPTEMBER 2003 VOL 301 SCIENCE



PRL 102, 016601 (2009)

PHYSICAL REVIEW LETTERS

week ending
9 JANUARY 2009

Giant Orbital Hall Effect in Transition Metals: Origin of Large Spin and Anomalous Hall Effects

H. Kontani,¹ T. Tanaka,¹ D. S. Hirashima,¹ K. Yamada,² and J. Inoue³

Recent review (cond-mat):

Theory of Spin Hall Effects in Semiconductors

Hans-Andreas Engel, Emmanuel I. Rashba, and Bertrand I. Halperin

February 3, 2008